

# FDD6676S

## 30V N-Channel PowerTrench<sup>®</sup> MOSFET

### General Description

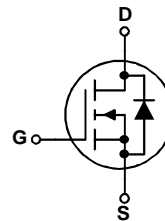
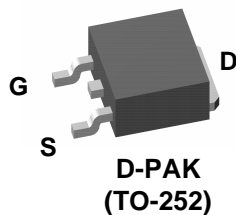
The FDS6676S is designed to replace a DPAK MOSFET and Schottky diode in synchronous DC:DC power supplies. This 30V MOSFET is designed to maximize power conversion efficiency, providing a low  $R_{DS(ON)}$  and low gate charge. The FDD6676S includes an integrated Schottky diode using Fairchild's monolithic SyncFET technology.

### Applications

- DC/DC converter

### Features

- 78 A, 30 V  $R_{DS(ON)} = 6.0 \text{ m}\Omega @ V_{GS} = 10 \text{ V}$   
 $R_{DS(ON)} = 7.1 \text{ m}\Omega @ V_{GS} = 4.5 \text{ V}$
- Low gate charge
- Fast Switching
- High performance trench technology for extremely low  $R_{DS(ON)}$



### Absolute Maximum Ratings $T_A=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Ratings	Units
$V_{DSS}$	Drain-Source Voltage	30	V
$V_{GSS}$	Gate-Source Voltage	$\pm 16$	V
$I_D$	Drain Current – Continuous (Note 3)	78	A
	– Pulsed (Note 1a)	100	
$P_D$	Power Dissipation for Single Operation (Note 1)	70	W
	(Note 1a)	3.1	
	(Note 1b)	1.3	
$T_J, T_{STG}$	Operating and Storage Junction Temperature Range	$-55$ to $+150$	$^\circ\text{C}$

### Thermal Characteristics

$R_{\theta JC}$	Thermal Resistance, Junction-to-Case (Note 1)	1.8	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient (Note 1a)	40	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient (Note 1b)	96	$^\circ\text{C/W}$

### Package Marking and Ordering Information

Device Marking	Device	Reel Size	Tape width	Quantity
FDD6676S	FDD6676S	13"	12mm	2500 units

**Electrical Characteristics** $T_A = 25^\circ\text{C}$  unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
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**Drain-Source Avalanche Ratings** (Note 2)

$W_{DSS}$	Drain-Source Avalanche Energy	Single Pulse, $V_{DD} = 15\text{ V}$ , $I_D = 16\text{ A}$			250	mJ
$I_{AR}$	Drain-Source Avalanche Current				16	A

**Off Characteristics**

$BV_{DSS}$	Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}$ , $I_D = 1\text{ mA}$	30			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = 10\text{ mA}$ , Referenced to $25^\circ\text{C}$		24		mV/ $^\circ\text{C}$
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS} = 24\text{ V}$ , $V_{GS} = 0\text{ V}$			500	$\mu\text{A}$
$I_{GSS}$	Gate-Body Leakage	$V_{GS} = \pm 16\text{ V}$ , $V_{DS} = 0\text{ V}$			$\pm 100$	nA

**On Characteristics** (Note 2)

$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}$ , $I_D = 1\text{ mA}$	1	1.3	3	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate Threshold Voltage Temperature Coefficient	$I_D = 10\text{ mA}$ , Referenced to $25^\circ\text{C}$		-0.9		mV/ $^\circ\text{C}$
$R_{DS(on)}$	Static Drain-Source On-Resistance	$V_{GS} = 10\text{ V}$ , $I_D = 16\text{ A}$ $V_{GS} = 4.5\text{ V}$ , $I_D = 15\text{ A}$ $V_{GS} = 10\text{ V}$ , $I_D = 16\text{ A}$ , $T_J = 125^\circ\text{C}$		4.6 5.2 7.2	6.0 7.1 9.0	m $\Omega$
$g_{FS}$	Forward Transconductance	$V_{DS} = 5\text{ V}$ , $I_D = 16\text{ A}$		79		S
$I_{D(on)}$	On-State Drain Current	$V_{GS} = 10\text{ V}$ , $V_{DS} = 5\text{ V}$	60			A

**Dynamic Characteristics**

$C_{iss}$	Input Capacitance	$V_{DS} = 15\text{ V}$ , $V_{GS} = 0\text{ V}$ , $f = 1.0\text{ MHz}$		4770		pF
$C_{oss}$	Output Capacitance			840		pF
$C_{rss}$	Reverse Transfer Capacitance			305		pF
$R_G$	Gate Resistance	$V_{GS} = 0\text{ V}$ , $f = 1.0\text{ MHz}$		1.5		$\Omega$

**Switching Characteristics** (Note 2)

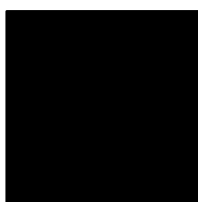
$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 15\text{ V}$ , $I_D = 1\text{ A}$ , $V_{GS} = 10\text{ V}$ , $R_{GEN} = 6\ \Omega$		13	23	ns
$t_r$	Turn-On Rise Time			13	23	ns
$t_{d(off)}$	Turn-Off Delay Time			86	138	ns
$t_f$	Turn-Off Fall Time			34	54	ns
$Q_g$	Total Gate Charge	$V_{DS} = 15\text{ V}$ , $I_D = 16\text{ A}$ , $V_{GS} = 5\text{ V}$		41	58	nC
$Q_{gs}$	Gate-Source Charge			10		nC
$Q_{gd}$	Gate-Drain Charge			10		nC

**Electrical Characteristics** (continued)  $T_A = 25^\circ\text{C}$  unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
<b>Drain–Source Diode Characteristics and Maximum Ratings</b>						
$I_S$	Maximum Continuous Drain–Source Diode Forward Current				3.5	A
$V_{SD}$	Drain–Source Diode Forward Voltage	$V_{GS} = 0\text{ V}, I_S = 3.5\text{ A}$ (Note 2)		385	700	mV
$t_{RR}$	Diode Reverse Recovery Time	$di_F/dt = 300\text{A}/\mu\text{s}, I_F = 16\text{A}$		29		ns
$I_{RM}$	Maximum Recovery Current			2.1		A
$Q_{RR}$	Diode Reverse Recovery Charge			30		nC

**Notes:**

- $R_{\theta JA}$  is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins.  $R_{\theta JC}$  is guaranteed by design while  $R_{\theta CA}$  is determined by the user's board design.



a)  $R_{\theta JA} = 40^\circ\text{C}/\text{W}$  when mounted on a  $1\text{ in}^2$  pad of 2 oz copper



b)  $R_{\theta JA} = 96^\circ\text{C}/\text{W}$  when mounted on a minimum pad.

Scale 1 : 1 on letter size paper

- Pulse Test: Pulse Width <  $300\mu\text{s}$ , Duty Cycle < 2.0%

- Maximum current is calculated as: 
$$\sqrt{\frac{P_D}{R_{DS(on)}}}$$

where  $P_D$  is maximum power dissipation at  $T_C = 25^\circ\text{C}$  and  $R_{DS(on)}$  is at  $T_{J(max)}$  and  $V_{GS} = 10\text{V}$ . Package current limitation is 21A

Typical Characteristics

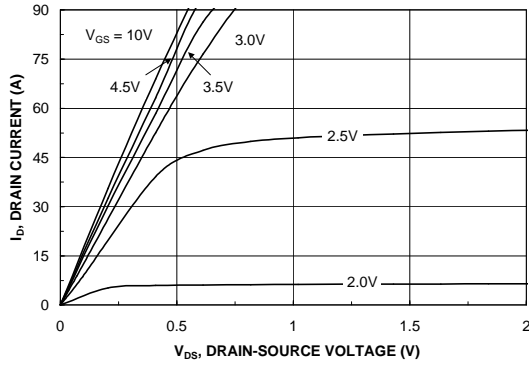


Figure 1. On-Region Characteristics

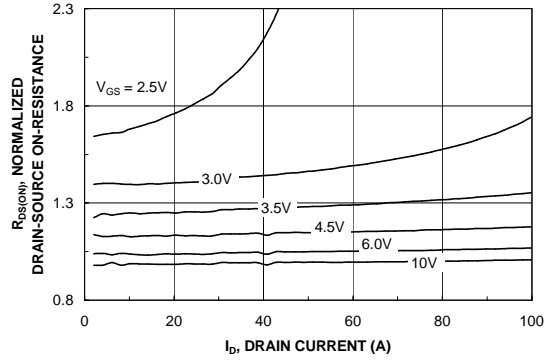


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage

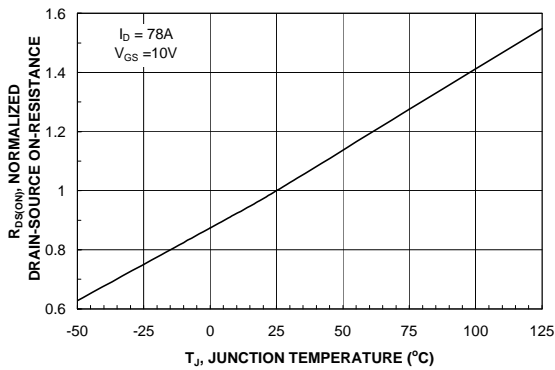


Figure 3. On-Resistance Variation with Temperature

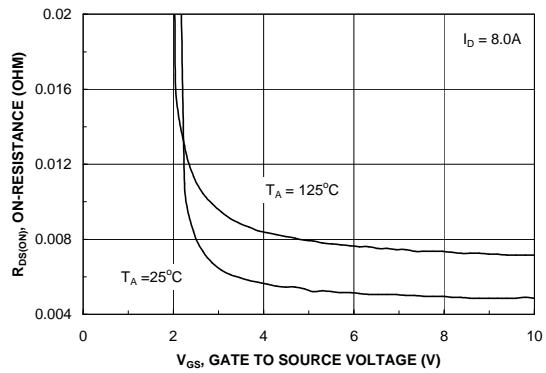


Figure 4. On-Resistance Variation with Gate-to-Source Voltage

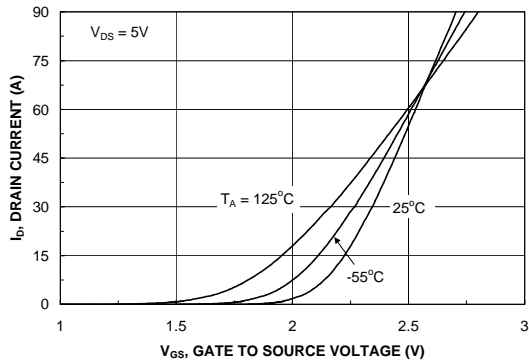


Figure 5. Transfer Characteristics

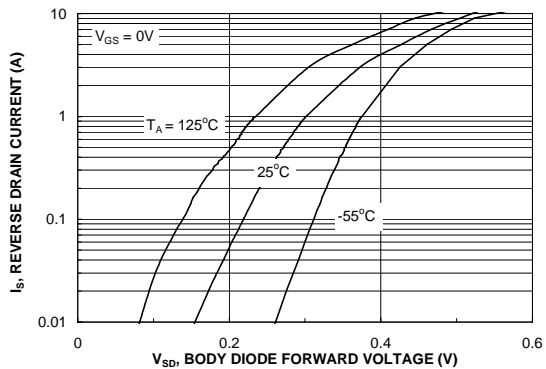


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature

Typical Characteristics

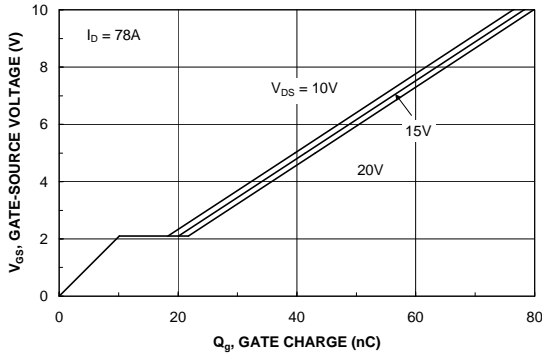


Figure 7. Gate Charge Characteristics

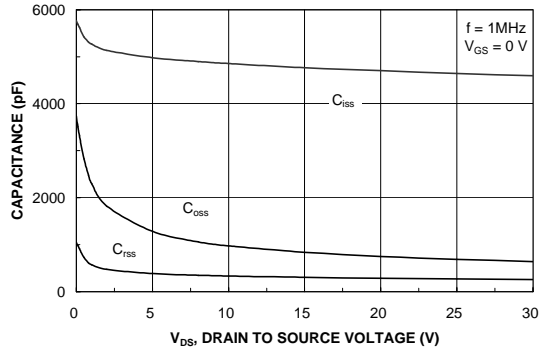


Figure 8. Capacitance Characteristics

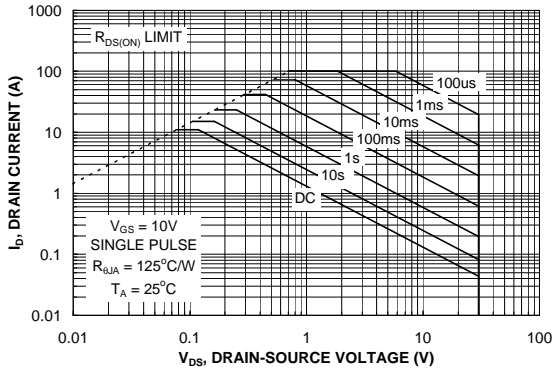


Figure 9. Maximum Safe Operating Area

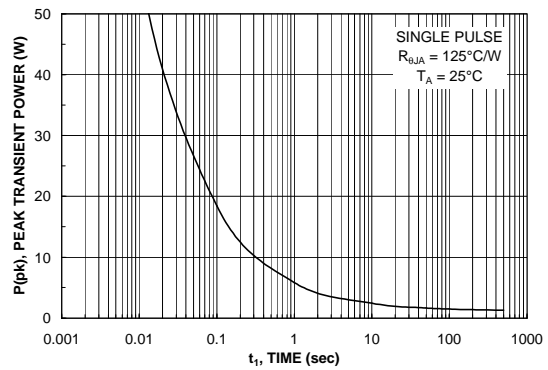


Figure 10. Single Pulse Maximum Power Dissipation

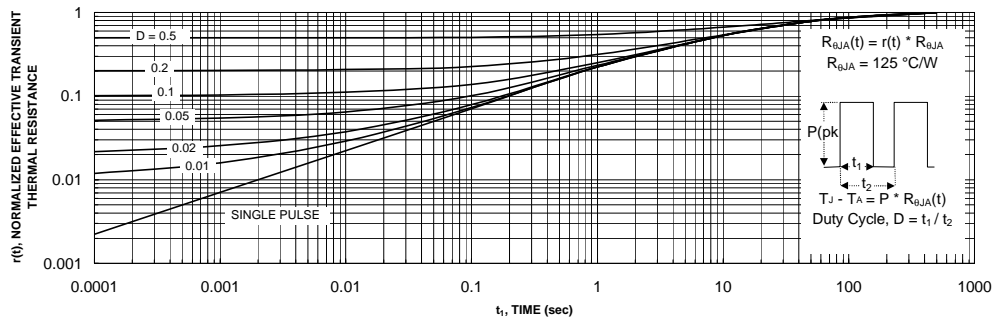


Figure 11. Transient Thermal Response Curve

Thermal characterization performed using the conditions described in Note 1b. Transient thermal response will change depending on the circuit board design.

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